

# PJQ2800

## 20V N-Channel Enhancement Mode MOSFET

**Voltage**

**20 V**

**Current**

**5.2A**

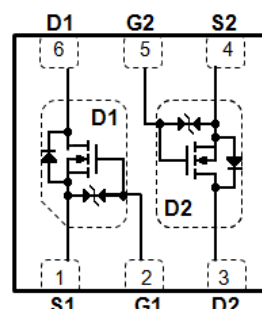
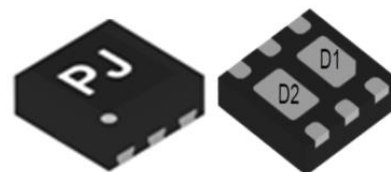
### Features

- RDS(ON) , VGS@4.5V, ID@5.2A<32mΩ
- RDS(ON) , VGS@2.5V, ID@3.2A<45mΩ
- RDS(ON) , VGS@1.8V, ID@2.0A<65mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- ESD Protected
- Lead free in compliance with EU RoHS 2011/65/EU directive.
- Green molding compound as per IEC61249 Std.  
(Halogen Free)

### Mechanical Data

- Case: DFN2020-6L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00032 ounces, 0.0093 grams
- Marking: 800

### DFN2020-6L



## Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	20	V
Gate-Source Voltage		V <sub>GS</sub>	±8	V
Continuous Drain Current		I <sub>D</sub>	5.2	A
Pulsed Drain Current		I <sub>DM</sub>	20.8	A
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	1.45	W
	Derate above 25°C		11.6	mW/°C
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance		R <sub>θJA</sub>	86	°C/W
- Junction to Ambient <sup>(Note 3)</sup>				

# PJQ2800

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.68	0.9	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =5.2A	-	24	32	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =3.2A	-	30	45	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =2.0A	-	40	65	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V	-	-0.01	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V	-	±3	±10	uA
Dynamic						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =5.2A, V <sub>GS</sub> =4.5V (Note 1,2)	-	6.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.0	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1.0MHZ	-	515	-	pF
Output Capacitance	C <sub>oss</sub>		-	60	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	47	-	
Switching						
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =10V, I <sub>D</sub> =5.2A, V <sub>GS</sub> =4.5V, R <sub>G</sub> =6Ω (Note 1,2)	-	7	-	ns
Turn-On Rise Time	tr		-	43	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	170	-	
Turn-Off Fall Time	tf		-	13	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>s</sub>	---	-	-	1.5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.77	1.2	V

### NOTES :

1. Pulse width≤300us, Duty cycle≤2%
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper
4. The maximum current rating is package limited

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## TYPICAL CHARACTERISTIC CURVES

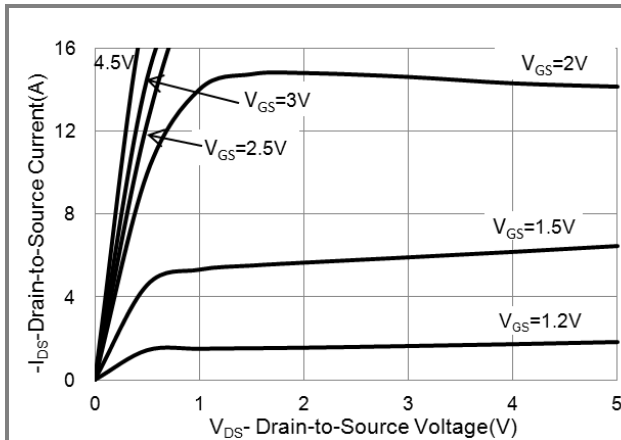


Fig.1 On-Region Characteristics

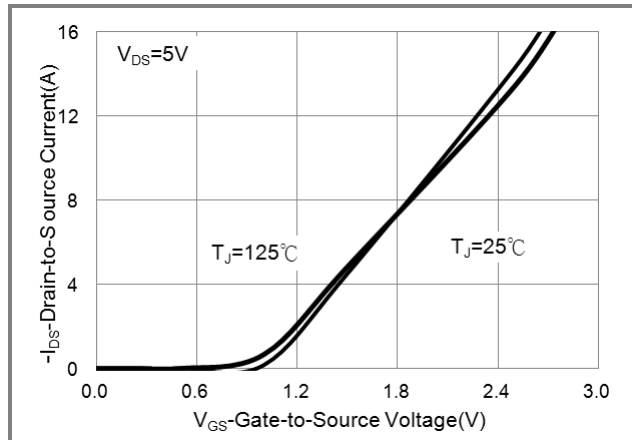


Fig.2 Transfer Characteristics

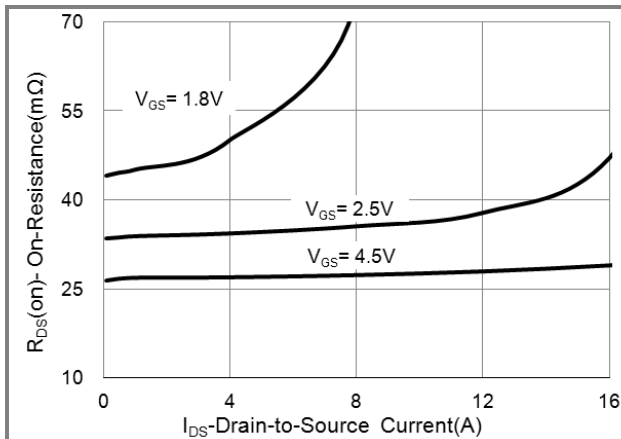


Fig.3 On-Resistance vs. Drain Current

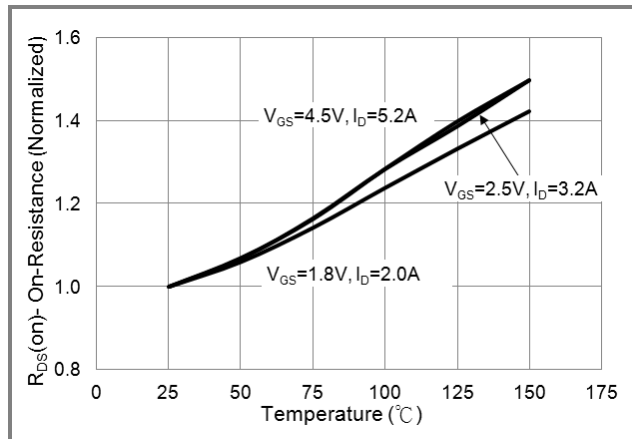


Fig.4 On-Resistance vs. Junction temperature

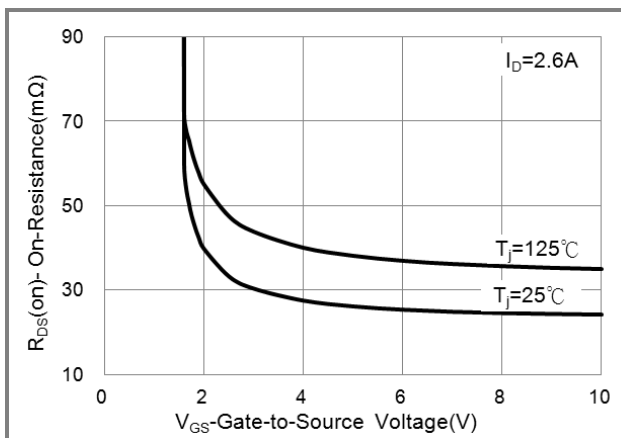


Fig.5 On-Resistance Variation with V\_GS.

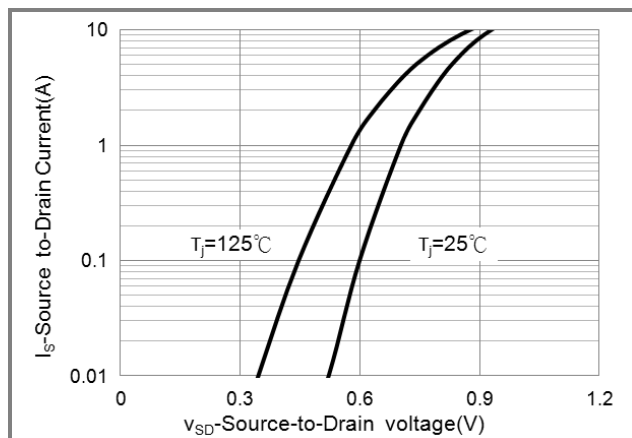


Fig.6 Body Diode Characteristics

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## TYPICAL CHARACTERISTIC CURVES

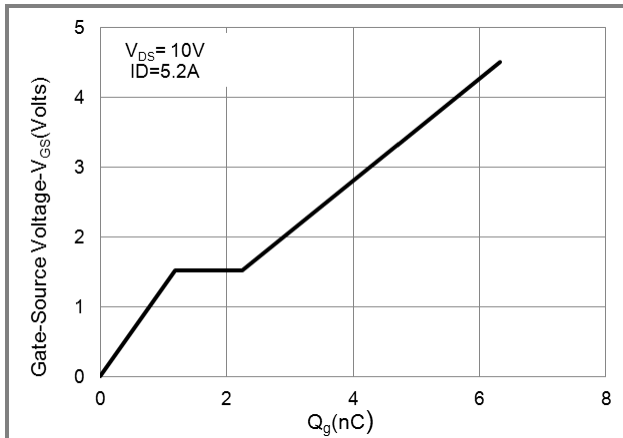


Fig.7 Gate-Charge Characteristics

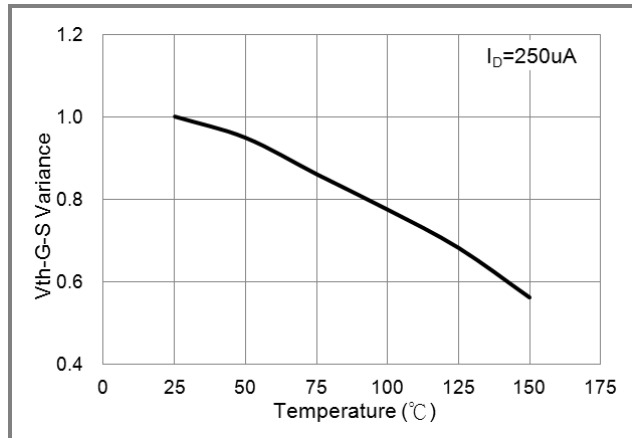


Fig.8 Threshold Voltage Variation with Temperature

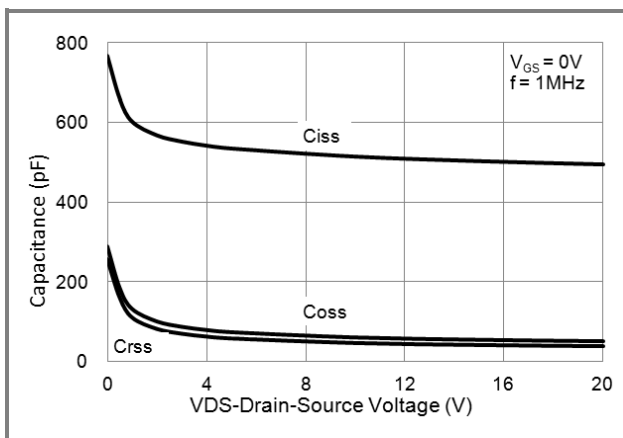


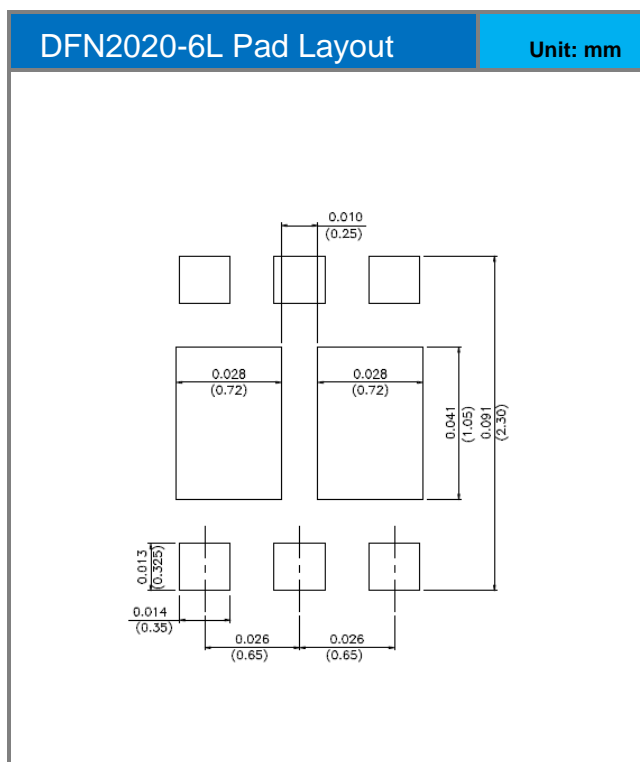
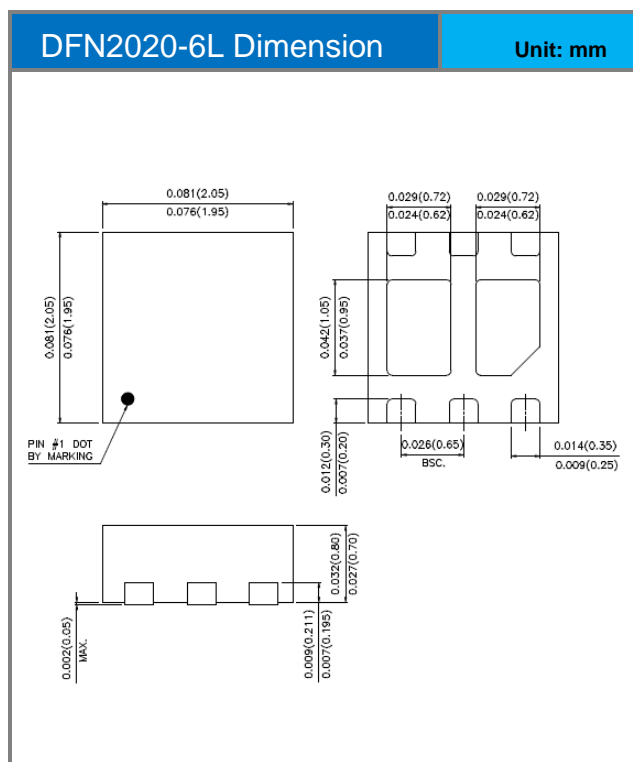
Fig.9 Capacitance vs. Drain-Source Voltage.

# PJQ2800

## Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJQ2800	DFN2020-6L	3K pcs / 7" reel	800

## Mounting Pad Layout



## PJQ2800

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